

NPN Silicon RF power transistor

MRF325

Description:

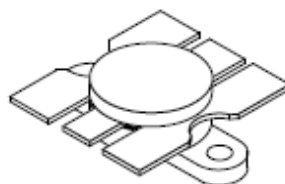
MRF325 is designed primarily for wideband large-signal output and driver amplifier stages in 100 to 500 MHz frequency range.

Specified 28 Volt, 400 MHz Characteristics
 Output Power = 30 Watts
 Minimum Gain = 8.5 dB
 Efficiency = 54% (Min)

Maximum Ratings:

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	V_{CEO}	33	Vdc
Collector–Base Voltage	V_{CBO}	60	Vdc
Emitter–Base Voltage	V_{EBO}	4.0	Vdc
Collector Current — Continuous — Peak	I_C	3.4 4.5	Adc
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ (1) Derate above 25°C	P_D	82 0.47	Watts $\text{W}/^\circ\text{C}$
Storage Temperature Range	T_{stg}	-65 to +150	$^\circ\text{C}$

Drawings:



SOT119/ CASE316